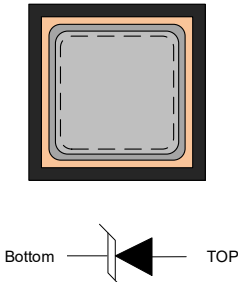


Mechanical Data

Layout(Top View)	Die Size($\mu\text{m} \times \mu\text{m}$)	350*350(including 50 μm Scribe)		
	Die Thickness(μm)	150 \pm 15		
	Scribe Line(μm)	50		
	Bonding PAD Size(μm^2)	Top	225*225	
	Top Metal (Anode)	Metallization	Al	
		Thickness(μm)	3.0 \pm 1.0	
	Bottom Metal (Cathode)	Metallization	Sn	
	Die Bonding Requirement (Recommendation)	/		
	Wafer Size(mm)	ϕ 150		
Die number : 125k / piece	Wire Bonding Requirement (Recommendation)	/		

Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Reverse Working Voltage	V_{RWM}	3.3	V
ESD Per IEC 61000-4-2(contact)	V_{ESD}	\pm 30	kV
Peak Pulse Current($t_p=8/20\mu\text{s}$)	I_{pp}	20	A
Operating Junction Temperature range	T_j	-55 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}	V_{RWM}			3.3	V
Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	4		7	V
Reverse Leakage Current	I_R	$V_{RWM}=3.3\text{V}$			1.0	μA
Forward Voltage	V_F	$I_F=10\text{mA}$			1.5	V
Clamping Voltage	V_C	$I_{pp}=20\text{A}, t_p=8/20\mu\text{s}$			15	V
Junction Capacitance	C_j	$V_R=0\text{V}, f=1\text{MHz}$			200	pF

Remarks:

- Wafer storage conditions (Recommendation) : Nitrogen protection, temperature $25\pm 5^{\circ}\text{C}$, Humidity $\leq 45\%$.
- This product manual is for reference only and is not part of the contract.

NOTICE

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